



THE CLAIMS:

A complete listing of the claims is as follows:

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cont

1. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate; and
a gate insulating film, provided on the semiconductor substrate, at least part of
which includes an insulating film containing metal, silicon and oxygen;
wherein [at least one of] fluorine is or [and] fluorine and nitrogen [is] are
contained in said insulating film containing metal, silicon and oxygen.
2. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate[:]; and
a gate insulating film provided on said semiconductor substrate, at least part of
said gate insulating film including a metal oxide film;
wherein an insulating film containing metal, silicon and oxygen is provided
between said semiconductor substrate and said metal oxide film and [at least one of] fluorine is
or fluorine and nitrogen [is] are contained in said insulating film containing metal, silicon and
oxygen.
3. (Currently Amended) A semiconductor device according to claim 1, [comprising:
[a semiconductor substrate;
a gate insulating film provided on said semiconductor substrate, at least part of
said gate insulating film including a metal oxide film;]

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wherein [an insulating film containing metal, silicon and oxygen is formed
between said semiconductor substrate and said metal oxide film and] each of said metal oxide
film and said insulating film containing metal, silicon and oxygen is an amorphous film.

4. (Original) A semiconductor device according to claim 3, further comprising a
flat insulating film having a gate opening portion in which said amorphous metal oxide film and
said gate insulating film containing metal, silicon and oxygen are formed; and a gate electrode
formed on said gate insulating film in the gate opening portion and having a surface which is
flush with said flat insulating film.

5. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
a gate insulating film provided on said semiconductor substrate, at least part of
said gate insulating film including a metal oxide film; and
wherein an insulating film containing metal, silicon and oxygen is formed
between said semiconductor substrate and said metal oxide film, said insulating film containing
fluorine or fluorine and nitrogen and a main metal element constituting said metal oxide film and
a main metal element constituting said insulating film containing metal, silicon and oxygen are
different from each other.

6. (Withdrawn)

7. (Withdrawn)

8. (Withdrawn)

9. (Withdrawn)

10. (Withdrawn)

11. (Withdrawn)

SUB B17 12. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate; and

first and second transistor regions formed on said semiconductor substrate, each

of said first and second transistor regions having a gate insulating film at least a part of which

includes an insulating film containing metal, silicon and oxygen, and at least one of said

insulating films provided in the first and second transistor regions contains fluorine or fluorine

and nitrogen;

wherein metal elements constituting said insulating films containing metal, silicon

and oxygen in said first and second regions are the same and the composition ratios of the metal

elements, silicon and oxygen of said insulating films containing metal, silicon and oxygen in said

first and second regions are different from each other.

13. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

a first transistor region on said semiconductor substrate, in which a metal oxide

film is provided as at least part of a first gate insulating film; and

a second transistor region on the semiconductor substrate in which a second gate insulating film containing metal, silicon and oxygen is provided [as at least part of the second gate insulating film], and a part of at least one of said first and second gate insulating films adjacent to the semiconductor substrate contain fluorine or fluorine and nitrogen;

wherein a metal element constituting the metal oxide film in said first transistor region is the same as a metal element constituting the second gate insulating film containing metal, silicon and oxygen in said second transistor region.

14. (Withdrawn)

15. (Withdrawn)

16. (Withdrawn)

17. (Withdrawn)

18. (Withdrawn)

19. (Withdrawn)

20. (Withdrawn)

Please add the following new claims:

21. (New) A semiconductor device according to claim 1, wherein the semiconductor substrate is made of silicon.
22. (New) A semiconductor device according to claim 2, wherein the semiconductor substrate is made of silicon.
23. (New) A semiconductor device comprising:
a semiconductor substrate; and
a gate insulating film provided on the semiconductor substrate, at least part of the gate insulating film including a metal oxide film;
wherein a single insulating film containing metal, silicon and oxygen is provided between the semiconductor substrate and the metal oxide film and at least one of fluorine and nitrogen is contained in the single insulating film containing metal, silicon and oxygen.
24. (New) A semiconductor device according to claim 5, wherein the semiconductor substrate is made of silicon.
25. (New) A semiconductor device according to claim 13, wherein the semiconductor substrate is made of silicon.

Please cancel claims 6 to 11 and 14 to 20 without prejudice or to create any estoppel as to equivalents.